

**LISTING OF CLAIMS**

1. (Currently Amended) A method of manufacturing an electric wiring of a semiconductor device including a semiconductor element formed on a semiconductor substrate and an aluminum alloy wiring connected to the semiconductor element on the semiconductor substrate, the method comprising:

forming an aluminum alloy layer on the semiconductor substrate, the aluminum alloy layer containing metal ~~which restricting an~~that restricts movement of aluminum;

forming TiN film on the aluminum alloy layer by using ~~spatteringsputtering~~, wherein a DC power of the ~~spatteringsputtering~~ is set to or less than  $5.5 \text{ W/cm}^2$  so that a formed TiN film ~~being~~ is rich with reactivity.

2. (Currently Amended) The method of manufacturing ~~an electric~~the electric wiring according to claim 1, wherein the TiN film is formed to have a thickness of 5 nm or more.

3. (Currently Amended) The method of manufacturing ~~an electric~~the electric wiring according to claim 1, wherein the TiN film is formed under a condition where a temperature of an atmosphere surrounding the semiconductor substrate during the ~~spatteringsputtering~~ is approximately  $180^\circ \text{ C}$  or less.

4. (Currently Amended) A method of manufacturing ~~an electric~~the electric wiring of a semiconductor device including a semiconductor element formed on a semiconductor substrate and an aluminum alloy wiring connected to the semiconductor element on the semiconductor substrate, the method comprising:

forming an aluminum alloy layer on the semiconductor substrate, the aluminum alloy layer containing metal ~~which restricting an~~ that restricts movement of aluminum;

forming TiN film on the aluminum alloy layer by using ~~sputteringsputtering~~, the ~~sputteringsputtering~~ being conducted using TiN as a target and being conducted without containing N<sub>2</sub> gas in an atmosphere surrounding the semiconductor substrate.

5. (Currently Amended) The method of manufacturing ~~an electric~~the electric wiring according to claim 1, wherein the ~~sputteringsputtering~~ is conducted using TiN, formed on a surface of a Ti target, as the target of the ~~sputteringsputtering~~.

6. (Currently Amended) The method of manufacturing ~~an electric~~the electric wiring according to claim 5, wherein the step of forming TiN film on the aluminum alloy layer including:

first ~~sputteringsputtering~~ the TiN film by using the TiN formed on the surface of the Ti target in the atmosphere without containing N<sub>2</sub> gas; and

second ~~sputteringsputtering~~ another TiN film on the TiN formed in the first ~~sputteringsputtering~~ in the atmosphere containing N<sub>2</sub> gas.

7. (Currently Amended) The method of manufacturing ~~an electric~~the electric wiring according to claim 4, wherein the step of forming TiN film on the aluminum alloy layer including:

first ~~sputteringsputtering~~ the TiN film by using the TiN formed on the surface of the Ti target in the atmosphere without containing N<sub>2</sub> gas; and

second ~~sputteringsputtering~~ another TiN film on the TiN formed in the first ~~sputteringsputtering~~ in the atmosphere containing N<sub>2</sub> gas, after the TiN is formed on an entire surface of the aluminum alloy layer in the first ~~sputteringsputtering~~.

8. (Currently Amended) The method of manufacturing ~~an electric~~the electric wiring according to claim 4, wherein the ~~sputteringsputtering~~ is conducted in a condition where a DC power of the ~~sputteringsputtering~~ is set to equal to or less than 5.5 W/cm<sup>2</sup> so that the formed TiN film is rich with reactivity.

Claims 9-15 (Canceled).